

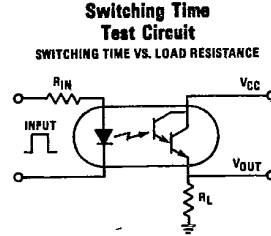
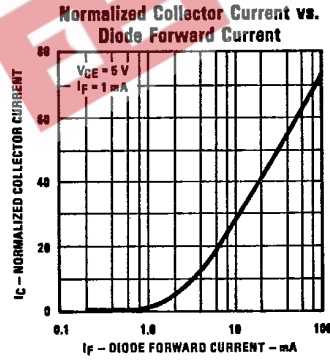
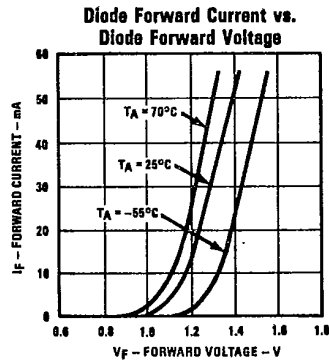
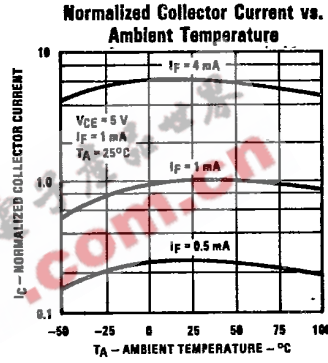
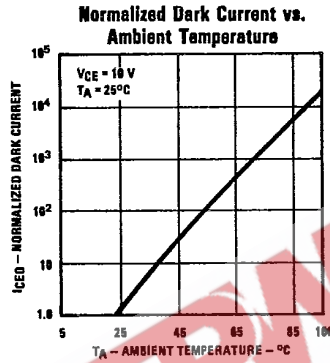
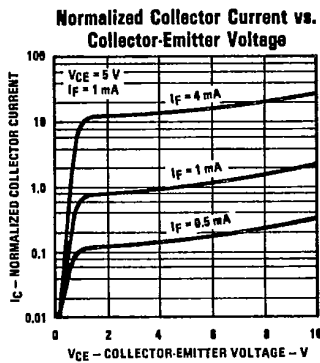
Types OPI3151, OPI3251

T-41-85

Electrical Characteristics (TA = 25°C unless otherwise noted)

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
Input Diode						
V _F	Forward Voltage			1.50	V	I _F = 10.0 mA
I _R	Reverse Current			100	μA	V _R = 3.0 V
Output Photodarlington						
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30			V	I _C = 100 μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage	30			V	I _C = 100 μA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	6.0			V	I _E = 100 μA
I _{CEO}	Collector-Emitter Dark Current			100	nA	V _{CE} = 10.0 V
Coupled						
I _C /I _F	DC Current Transfer Ratio	300			%	I _F = 10.0 mA, V _{CE} = 1.00 V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage			1.20	V	I _F = 10.0 mA, I _C = 30 mA, I _B = 0
t _r	Output Rise Time		3.0		μs	V _{CC} = 10.0 V, I _C = 10.0 mA, R _L = 100Ω
t _f	Output Fall Time		25		μs	See Test Circuit

Typical Performance Curves



NOTE: Rise Time (t_r) is time required for collector current to increase from 10% to 90% of its final value. Fall Time (t_f) is time required for the collector current to decrease from 90% to 10% of its initial value.